

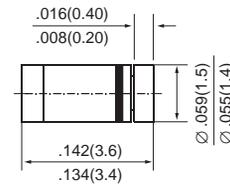
**SCHOTTKY DIODES**

**FEATURES**

- \* Fast Switching Device( $T_{RR}<4.0nS$ )
- \* Mini MELF Glass Case (SOD-80)
- \* Through-Hole Device Type Mounting
- \* Hermetically Sealed Glass
- \* Compression Bonded Construction
- \* All external surfaces are corrosion resistant and leads are readily solderable



**SOD-80**



**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

**MAXIMUM RATINGS** ( @  $T_A = 25^\circ C$  unless otherwise noted )

RATINGS	SYMBOL	BAS85	UNITS
Maximum Forward Continuous Reverse Voltage	$V_R$	30	V
Maximum Forward Continuous Current @ $T_A=25^\circ C$	$I_F$	200	mAmps
Maximum Peak Forward Current @ $T_A=25^\circ C$	$I_{FM}$	300	mAmps
Surge Forward Current @ $t_p<1s, T_A=25^\circ C$	$I_{FSM}$	600	mAmps
Maximum Power Dissipation @ $T_A=65^\circ C$	$P_D$	200	mW
Junction Temperature	$T_J$	125	$^\circ C$
Storage Temperature Range	$T_{STG}$	-65 to + 150	$^\circ C$

**ELECTRICAL CHARACTERISTICS** ( @  $T_A = 25^\circ C$  unless otherwise noted )

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Reverse breakdown voltage ( $I_R=10\mu A$ )	$V_{(BR)R}$	30	-	-	V
Reverse voltage leakage current ( $V_R=25V$ )	$I_R$	-	-	2	$\mu A$
Forward voltage Pulse Test $t_p<300\mu s, \delta<2\%$	$V_F$	-	( $I_F=0.1mA$ )	0.24	V
			( $I_F=1mA$ )	0.32	
			( $I_F=10mA$ )	0.4	
			( $I_F=30mA$ )	0.5	
			( $I_F=100mA$ )	0.8	
Diode capacitance ( $V_R=1, f=1MHz$ )	$C_D$	-	-	10	pF
Revers recovery time ( $I_F=I_R=10mA, I_R=1mA$ )	$t_{rr}$	-	-	5	nS